

D. A. Tenne's list of scientific publications

Book chapter:

A. Milekhin, D.A. Tenne, D.R.T. Zahn, Quantum dot structures: Raman and infrared spectroscopy, in *Quantum Dots and Nanowires*, edited by S. Bandyopadhyay and H. S. Nalwa (American Scientific Publishers, 2003), pp. 375–419.

Journals:

1. Y. Sakaguchi, D. A. Tenne, and M. Mitkova, Oxygen-assisted photoinduced structural transformation in amorphous Ge-S films — *Phys. Status Solidi B* **246**, No. 8, 1813–1819 (2009).
2. Y. Sakaguchi, D. A. Tenne, and M. Mitkova, Structural development in Ge-rich Ge-S glasses — *Journal of Non-Crystalline Solids* (2009), in press, doi:10.1016/j.jnoncrysol.2009.04.064.
3. D. A. Tenne, H. N. Lee, R. S. Katiyar, and X. X. Xi, Ferroelectric phase transitions in three-component short-period superlattices studied by ultraviolet Raman spectroscopy — *J. Appl. Phys.* **105**, 054106 (2009).
4. H. Wang, D. Wingett, M. H. Engelhard, K. Feris, K. M. Reddy, P. Turner, J. Layne, C. Hanley, J. Bell, D. Tenne, C. Wang, A. Punnoose, Fluorescent dye encapsulated ZnO particles with cell-specific toxicity for potential use in biomedical applications — *J. Mater. Sci.: Mater. Med.* **20**, 11–22 (2009).
5. D. A. Tenne and X. X. Xi, Raman spectroscopy of ferroelectric thin films and superlattices — *Journal of the American Ceramic Society*, **91**, 1820–1834 (2008).
6. A. Soukiassian, W. Tian, V. Vaithyanathan, J. H. Haeni, L. Q. Chen, X. X. Xi, D. G. Schlom, D. A. Tenne, H. P. Sun, X. Q. Pan, K. J. Choi, C. B. Eom, Y. L. Li, Q. X. Jia, C. Constantin, R. M. Feenstra, M. Bernhagen, P. Reiche, and R. Uecker, Growth of nanoscale BaTiO₃/SrTiO₃ superlattices by molecular-beam epitaxy — *Journal of Materials Research*, **23**, 1417–1432 (2008).
7. Y. L. Li, S. Y. Hu, D. Tenne, A. Soukiassian, D. G. Schlom, L. Q. Chen, X. X. Xi, K. J. Choi, C. B. Eom, A. Saxena, T. Lookman, and Q. X. Jia, Interfacial coherency and ferroelectricity of BaTiO₃/SrTiO₃ superlattice films — *Appl. Phys. Lett.* **91**, 252904 (2007).
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9. D. A. Tenne, I. E. Gonenli, A. Soukiassian, D. G. Schlom, S. M. Nakhmanson, K. M. Rabe, and X. X. Xi, Raman study of oxygen reduced and re-oxidized strontium titanate — *Phys. Rev. B*, **76**, 024303 (2007).
10. A. Bruchhausen, N. D. Lanzillotti-Kimura, A. Fainstein, A. Soukiassian, D. A. Tenne, D. Schlom, X. X. Xi, and A. Cantarero, Acoustic properties of nanoscale oxide heterostructures probed by UV Raman spectroscopy — *Journal of Physics: Conference Series* **92**, 012160 (2007).
11. A. Soukiassian, W. Tian, D. A. Tenne, X. X. Xi, D. G. Schlom, N. D. Lanzillotti-Kimura, A. Bruchhausen, A. Fainstein, H. P. Sun, X. Q. Pan, A. Cros, and A. Cantarero, Acoustic Bragg mirrors and cavities made using piezoelectric oxides — *Appl. Phys. Lett.* **90**, 042909 (2007).
12. D. A. Tenne, A. Bruchhausen, N. D. Lanzillotti-Kimura, A. Fainstein, R. S. Katiyar, A. Cantarero, A. Soukiassian, V. Vaithyanathan, J. H. Haeni, W. Tian, D. G. Schlom, K. J. Choi, D. M. Kim, C. B. Eom, H. P. Sun, X. Q. Pan, Y. L. Li, L. Q. Chen, Q. X. Jia, S. M. Nakhmanson, K. M. Rabe,

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14. A. Venimadhav, A. Soukiassian, D. A. Tenne, Qi Li, X. X. Xi, D. G. Schlom, R. Arroyave, Z. K. Liu, H. P. Sun, X. Q. Pan, M. Lee, and N. P. Ong, Structural and transport properties of epitaxial Na_xCoO₂ thin films — *Appl. Phys. Lett.* **87**, 172104 (2005).
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International Conference Proceedings:

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